

DIGITAL AUDIO MOSFET

Features

- Integrated Half-Bridge Package
- Reduces the Part Count by Half
- Facilitates Better PCB Layout
- Key Parameters Optimized for Class-D Audio Amplifier Applications
- Low $R_{DS(ON)}$ for Improved Efficiency
- Low Q_g and Q_{sw} for Better THD and Improved Efficiency
- Low Q_{rr} for Better THD and Lower EMI
- Can Delivery up to 200W per Channel into 8Ω Load in Half-Bridge Configuration Amplifier
- Lead-Free Package

Key Parameters ⑥		
V_{DS}	150	V
$R_{DS(ON)}$ typ. @ 10V	80	m Ω
Q_g typ.	13	nC
Q_{sw} typ.	4.1	nC
$R_{G(int)}$ typ.	2.5	Ω
T_J max	150	$^{\circ}$ C



G1, G2	D1, D2	S1, S2
Gate	Drain	Source

Description

This Digital Audio MosFET Half-Bridge is specifically designed for Class D audio amplifier applications. It consists of two power MosFET switches connected in half-bridge configuration. The latest process is used to achieve low on-resistance per silicon area. Furthermore, Gate charge, body-diode reverse recovery, and internal Gate resistance are optimized to improve key Class D audio amplifier performance factors such as efficiency, THD and EMI. These combine to make this Half-Bridge a highly efficient, robust and reliable device for Class D audio amplifier applications.

Absolute Maximum Ratings ⑥

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	150	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ $T_C = 25^{\circ}$ C	Continuous Drain Current, V_{GS} @ 10V	8.7	A
I_D @ $T_C = 100^{\circ}$ C	Continuous Drain Current, V_{GS} @ 10V	6.2	
I_{DM}	Pulsed Drain Current ①	34	
E_{AS}	Single Pulse Avalanche Energy②	77	mJ
P_D @ $T_C = 25^{\circ}$ C	Power Dissipation ④	18	W
P_D @ $T_C = 100^{\circ}$ C	Power Dissipation ④	7.2	
	Linear Derating Factor	0.15	W/ $^{\circ}$ C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	$^{\circ}$ C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

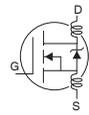
Thermal Resistance ⑥

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	6.9	
$R_{\theta JA}$	Junction-to-Ambient ④	—	65	

Notes ① through ⑥ are on page 2

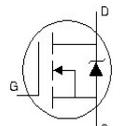
Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified) ⑥

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.19	—	$V/^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	80	95	$m\Omega$	$V_{GS} = 10V, I_D = 5.2A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	4.9	V	$V_{DS} = V_{GS}, I_D = 50\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-11	—	$mV/^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 150V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 150V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	11	—	—	S	$V_{DS} = 50V, I_D = 5.2A$
Q_g	Total Gate Charge	—	13	20	nC	$V_{DS} = 75V$ $V_{GS} = 10V$ $I_D = 5.2A$ See Fig. 6 and 19
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	3.3	—		
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	0.8	—		
Q_{gd}	Gate-to-Drain Charge	—	3.9	—		
Q_{godr}	Gate Charge Overdrive	—	5.0	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	4.1	—		
$R_{G(int)}$	Internal Gate Resistance	—	2.5	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	7.0	—	ns	$V_{DD} = 75V, V_{GS} = 10V$ ③ $I_D = 5.2A$ $R_G = 2.4\Omega$
t_r	Rise Time	—	6.6	—		
$t_{d(off)}$	Turn-Off Delay Time	—	13	—		
t_f	Fall Time	—	3.1	—		
C_{iss}	Input Capacitance	—	810	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$, See Fig.5 $V_{GS} = 0V, V_{DS} = 0V$ to $120V$
C_{oss}	Output Capacitance	—	100	—		
C_{rfs}	Reverse Transfer Capacitance	—	15	—		
C_{oss}	Effective Output Capacitance	—	97	—		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		



Diode Characteristics ⑥

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S @ T_C = 25^\circ\text{C}$	Continuous Source Current (Body Diode)	—	—	8.7	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	34		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 5.2A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	57	86	ns	$T_J = 25^\circ\text{C}, I_F = 5.2A$
Q_{rr}	Reverse Recovery Charge	—	140	210	nC	$di/dt = 100A/\mu s$ ③



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 5.8\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 5.2A$.
- ③ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.

④ R_{θ} is measured at T_J of approximately 90°C .

⑤ Limited by T_{jmax} . See Figs. 14, 15, 17a, 17b for repetitive avalanche information

⑥ Specifications refer to single MosFET.

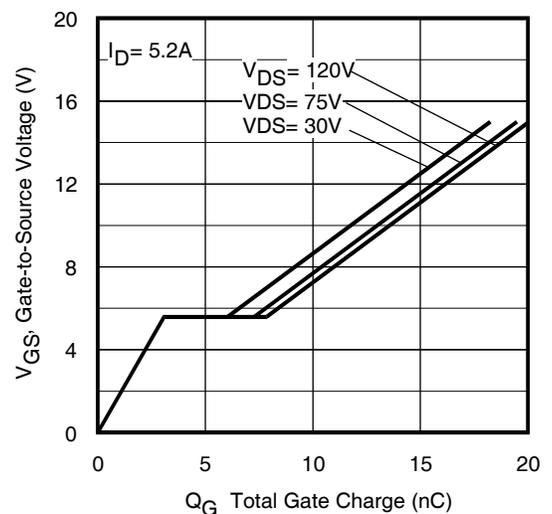
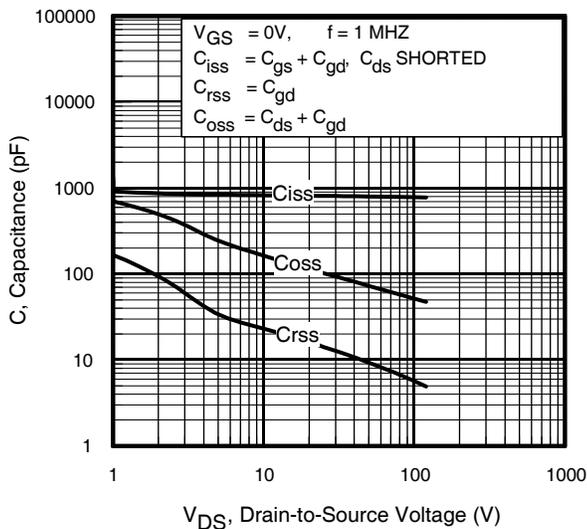
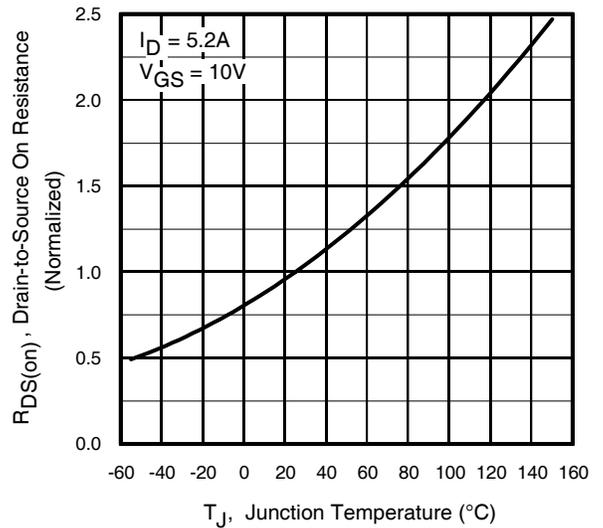
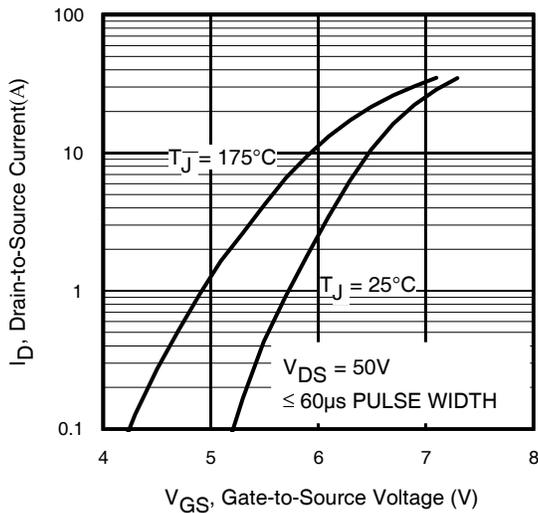
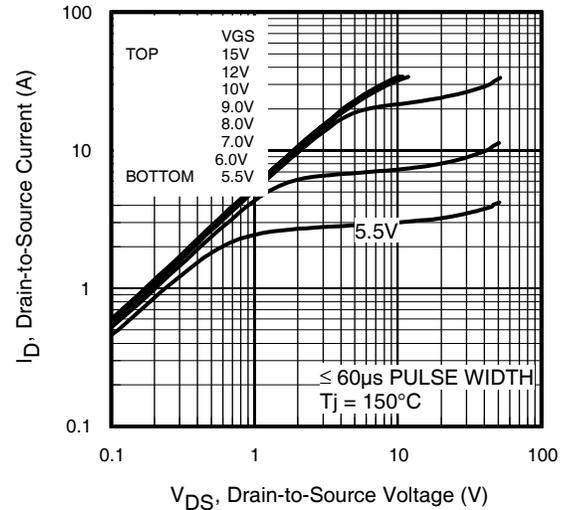
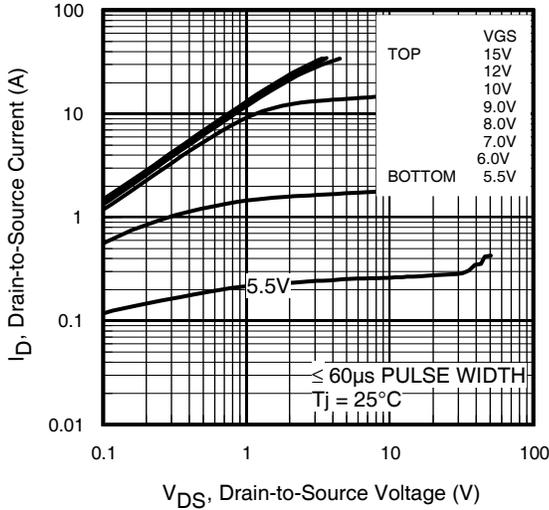


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage
www.irf.com

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

IRFI4019H-117P

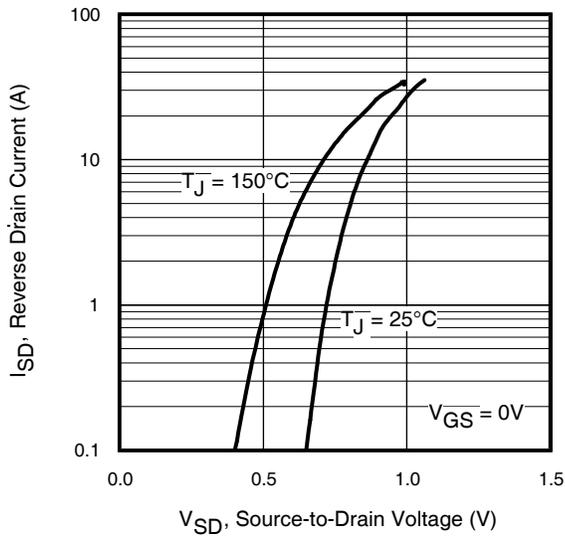


Fig 7. Typical Source-Drain Diode Forward Voltage

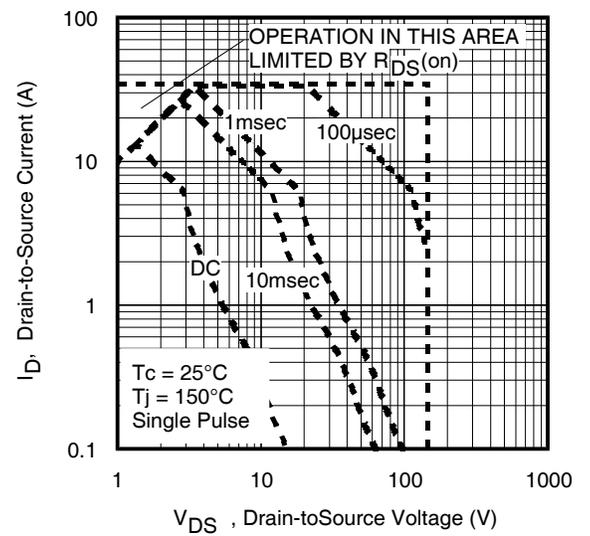


Fig 8. Maximum Safe Operating Area

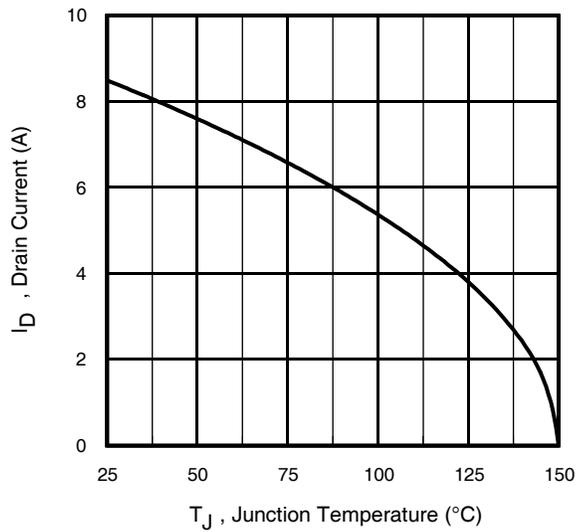


Fig 9. Maximum Drain Current vs. Case Temperature

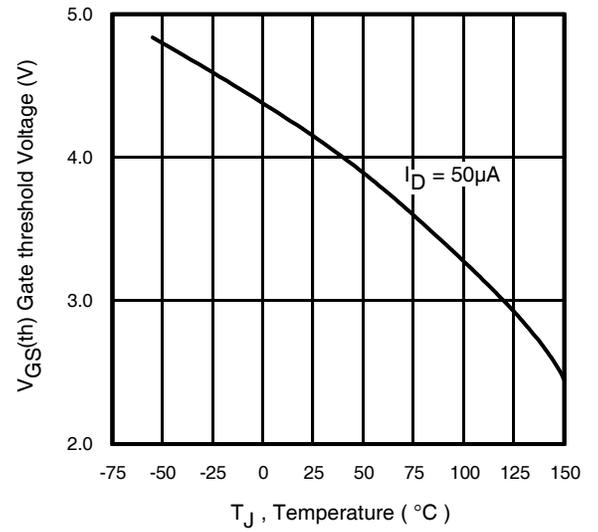


Fig 10. Threshold Voltage vs. Temperature

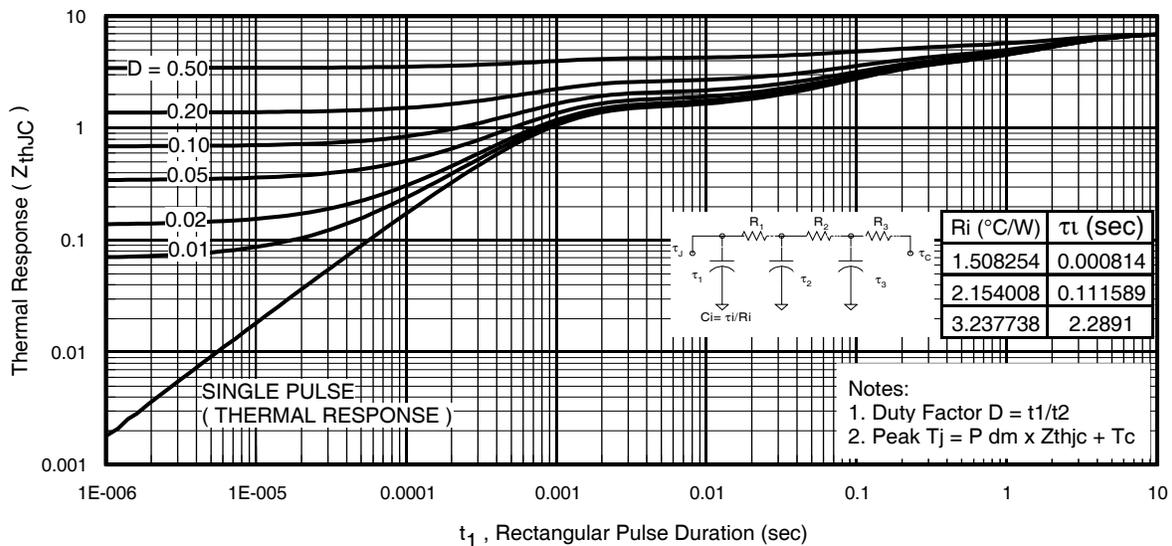


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

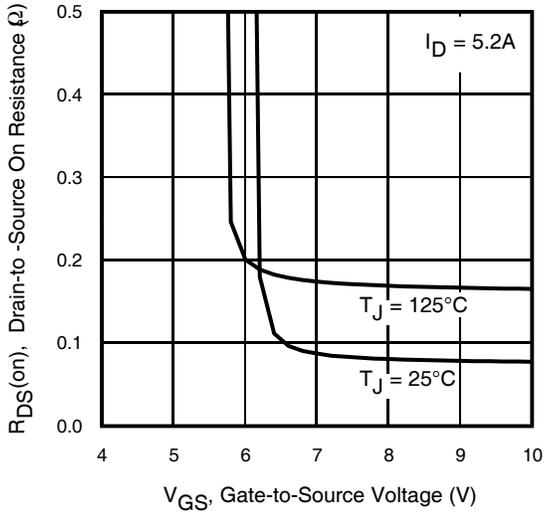


Fig 12. On-Resistance Vs. Gate Voltage

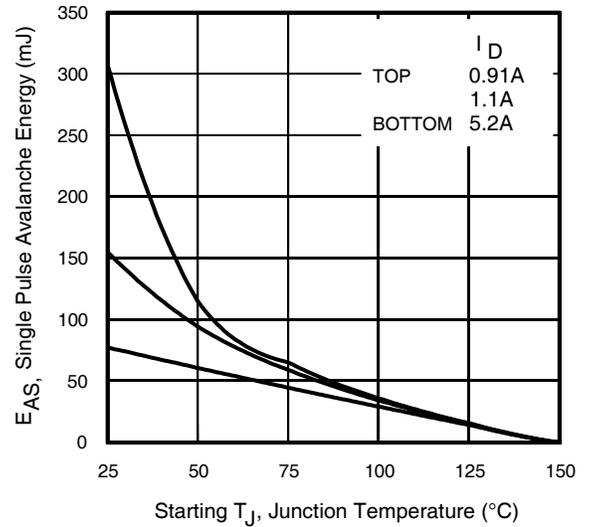


Fig 13. Maximum Avalanche Energy Vs. Drain Current

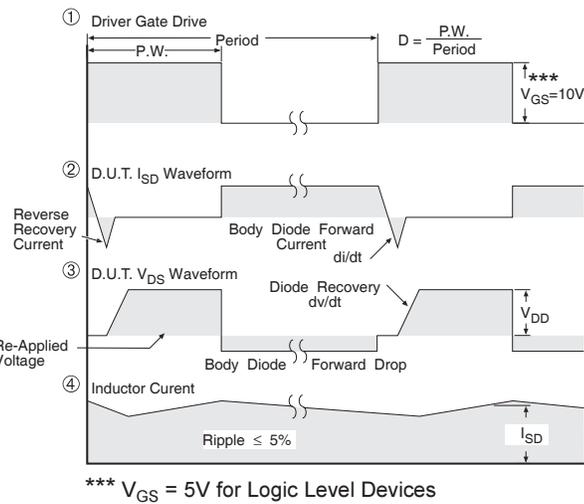
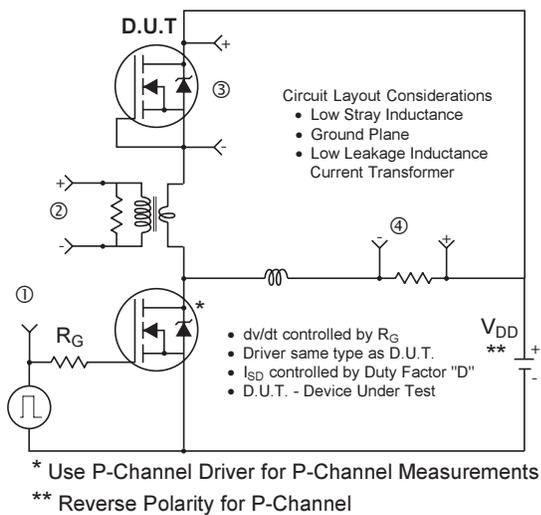


Fig 14. Diode Reverse Recovery Test Circuit for HEXFET® Power MOSFETs

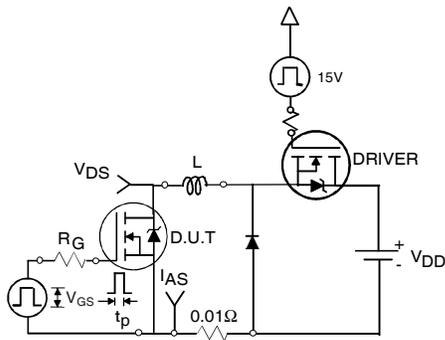


Fig 15a. Unclamped Inductive Test Circuit

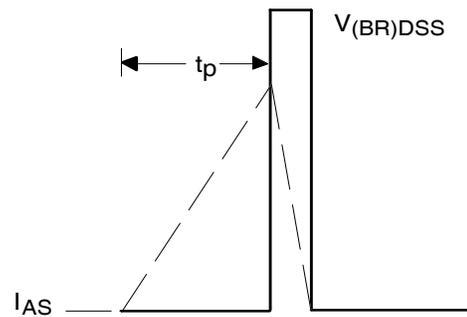


Fig 15b. Unclamped Inductive Waveforms

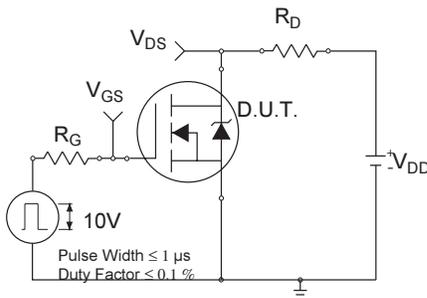


Fig 16a. Switching Time Test Circuit

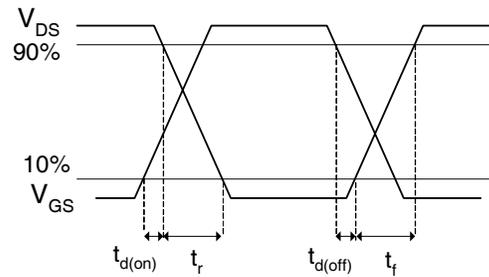


Fig 16b. Switching Time Waveforms

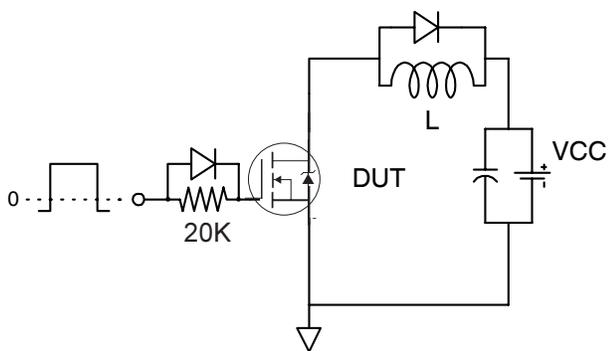


Fig 17a. Gate Charge Test Circuit

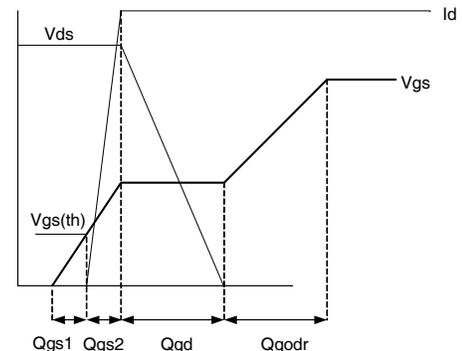


Fig 17b Gate Charge Waveform

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.